

PRODUCT DESCRIPTION

This retro-reflective sensor combines an infrared emitting diode and a unique photodarlington output to provide high sensitivity while rejecting ambient light. It has a very long sensing range (up to 4 inches) compared to ordinary retros.

The output of this sensor is activated when a reflective surface is brought into its field of view.

The sensor housing is molded polycarbonate with a slotted flange for easy mounting.

FEATURES

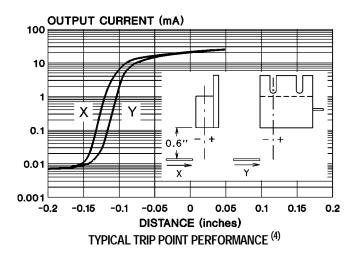
- Low Cost
- · Small Package Size
- Long Sensing Range (up to 4 inches)
- Detects Low/Diffuse Reflectance
 Surfaces

SPECIFICATIONS @ 25°C

Parameter	Symbol	Min.	Тур.	Max.	Units
Output Current I _F = 20 mA ⁽⁵⁾	Ι _P	6	15		mA
Ambient Sensitivity I _F = 0 mA ^{(1) (2)}	I _A		30	100	μΑ
Crosstalk $I_F = 20 \text{ mA}^{(3)}$	I _{CX}		5	30	μΑ
Output Saturation Voltage $I_F = 20 \text{ mA}^{(1)} I_P = 10 \text{ mA}$	V_{SAT}		0.9	1.2	V

NOTES

- Distance to 90% reflectance paper = 0.6", V_{CF} = 5V.
- 2. 100 fc fluorescent light incident upon target surface.
- 3. No target surface.
- 4. Referenced to optical centerline of sensor, $V_{CF} = 5V$, IF = 20 mA.
- 5. Distance to 90% reflectance paper = 2.0", $V_{CE} = 5V$.

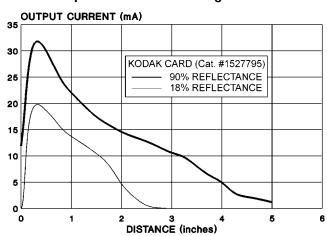


ABSOLUTE MAXIMUM RATINGS @ 25°C UNLESS NOTED

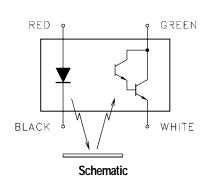
Parameter	Symbol	Rating	Units			
Temperature Range						
Operating	T _A	-40 to +85	°C			
Storage	T _S	-40 to +85	°C			
Continuous Emitter Current	I _F	40	mA			
Output Power Dissipation (derate 1.36 mW/°C above 30°C)						
IR Emitter	P _{D EMITTER}	75	mW			
IR Detector	P _{D DETECTOR}	75	mW			
Emitter Reverse Voltage	V_{R}	2.0	V			
Detector Voltage	V _{CE}	30	V			

TYPICAL PERFORMANCE CURVES @ 25°C

Output Current vs. Sensing Distance



PACKAGE DIMENSIONS inches (mm)



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